

FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)			Docket Number: 3165.41USUI	Application Number: 10/723,382
			Applicant: MUNNS	
			Filing Date: 11/25/2003	Group Art Unit: 2815

O I P E S C I
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EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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▼	6,489,628 B1	12/03/2002	Morizuka			

EXAMINER <i>Matthew Wan</i>	DATE CONSIDERED <i>5/12/06</i>
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<i>Mew</i>	6,583,454 B2	06/24/2003	Sheppard et al.			
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<i>Mew</i>		Amano, H. et al., "Effects of the buffer layer in metalorganic vapour phase epitaxy of GaN on sapphire substrate," <i>Thin Solid Films</i> , Vol. 163, pp. 415-420 (1988)
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		Hsu, L. et al., "Effect of polarization fields on transport properties in AlGaN/GaN heterostructures," <i>Journal of Applied Physics</i> , Vol. 89 No. 3, pp. 1783-1789 (February 1, 2001)
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EXAMINER <i>Matthew Man</i>	DATE CONSIDERED <i>5/12/06</i>
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<i>Mew</i>		Khan, M. et al., "Properties and ion implantation of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ epitaxial single crystal films prepared by low pressure metalorganic chemical vapor deposition," <i>Appl. Phys. Lett.</i> , Vol. 43, No. 5, pp. 492-494 (September 1, 1983)
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<i>Munns</i>		Smorchkova, I. et al., "AlN/GaN and (Al,Ga)N/AlN/GaN two-dimensional electron gas structures grown by plasma-assisted molecular-beam epitaxy," <i>Journal of Applied Physics</i> , Vol. 90, No. 10, pp. 5196-5201 (November 15, 2001)
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EXAMINER <i>Murphy</i>	DATE CONSIDERED 5/12/06
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